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## N-Channel UniFET<sup>TM</sup> FRFET<sup>®</sup> MOSFET **500 V, 24 A, 200 m**Ω

#### **Features**

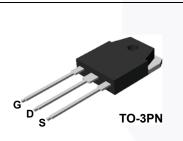
- R<sub>DS(on)</sub> = 166 mΩ (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 12 A
- Low Gate Charge (Typ. 65 nC)
- Low C<sub>rss</sub> (Typ. 32 pF)
- 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

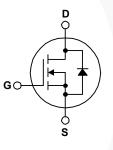
#### Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET® MOSFET has been enhanced by lifetime control. Its trr is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





#### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

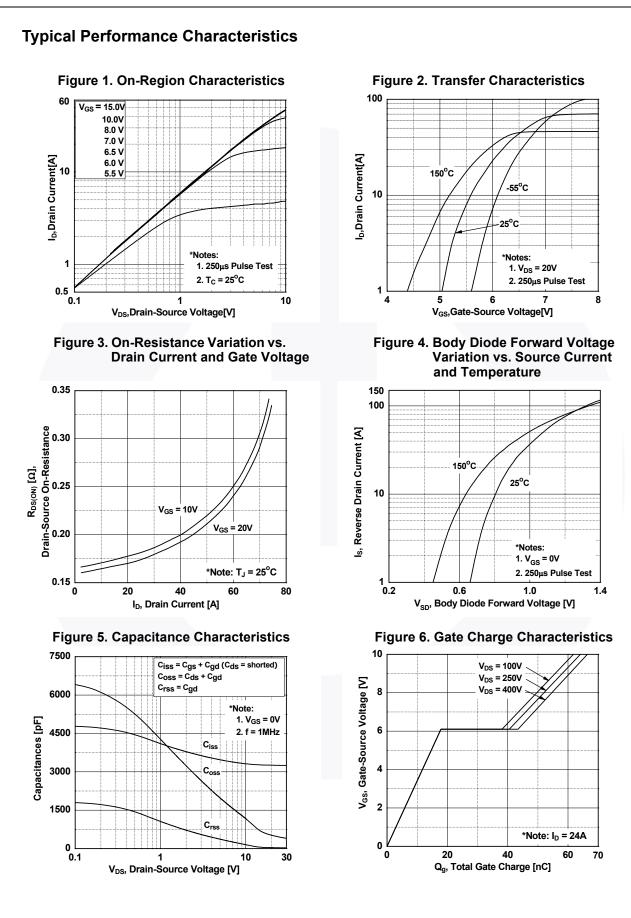
Symbol		FDA24N50F	Unit			
V <sub>DSS</sub>	Drain to Source Voltage	500	V			
V <sub>GSS</sub>	Gate to Source Voltage			±30	V	
ID	Drain Current	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		24		
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		14	A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	96	Α	
E <sub>AS</sub>	Single Pulsed Avalanche Energy			1872	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	24	Α	
E <sub>AR</sub>	Repetitive Avalanche Energ	lУ	(Note 1)	27	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20	V/ns		
P <sub>D</sub>	Deven Dississation	(T <sub>C</sub> = 25 <sup>o</sup> C)		270	W	
	Power Dissipation	- Derate Above 25°C		2.2	W/ºC	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

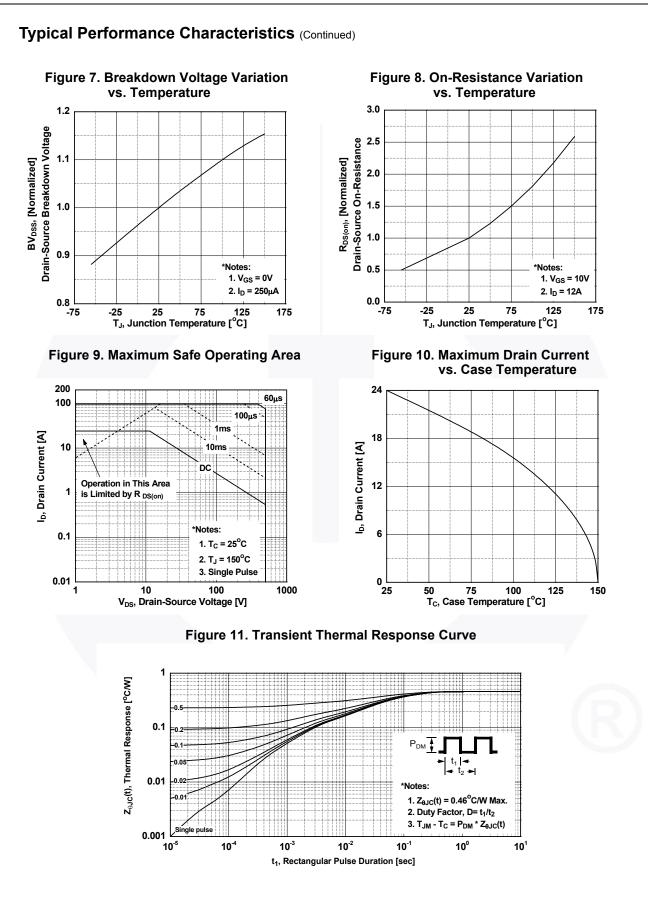
#### **Thermal Characteristics**

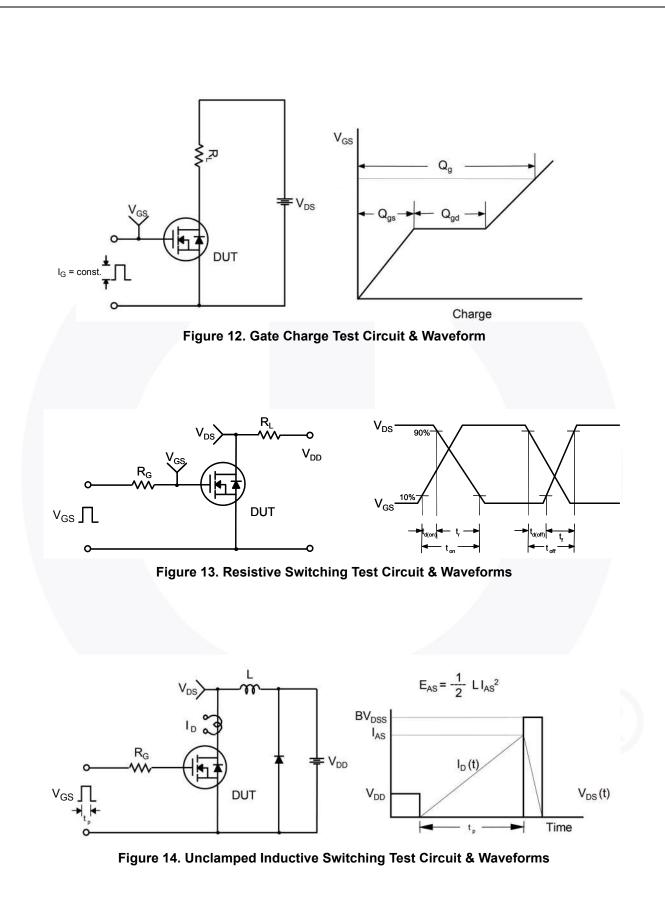
Symbol	Parameter	FDA24N50F	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.46	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/w

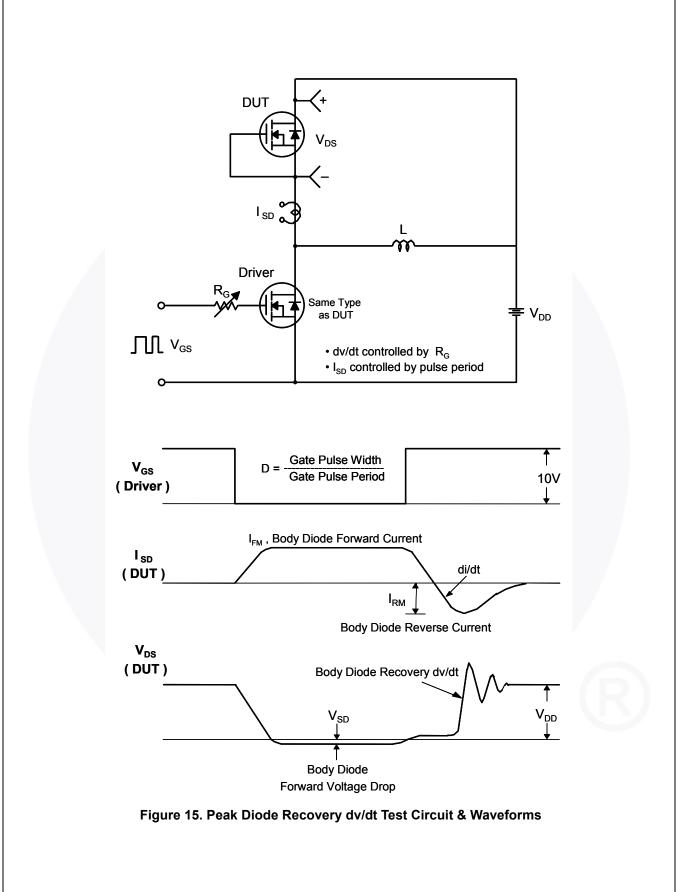
		Top Mark	Package	Packing Method	Reel Size	e Ta	ape Width	Qua	antity
		TO-3PN			N/A		30 units		
Electrical	Chara	icteristics T <sub>C</sub> = 25°C u	unless other	wise noted.					
Symbol		Parameter		Test Conditions	s	Min.	Тур.	Max.	Unit
Off Charac	teristics								
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage		lo =	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25 <sup>o</sup> C		500	-	_	V
∆BV <sub>DSS</sub>	Breakdown Voltage Temperature Coefficient					000			
$/\Delta T_J$			I <sub>D</sub> =	$I_D$ = 250 $\mu$ A, Referenced to 25°C			0.6	-	V/ºC
	Zoro Cat	Zara Cata Valtaga Drain Current		V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V		-	-	1	
I <sub>DSS</sub> Zero (		o Gate Voltage Drain Current		V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125 <sup>o</sup> C		-	-	10	- μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current		V <sub>GS</sub>	s = ±30 V, V <sub>DS</sub> = 0 V		-	-	±100	nA
On Charact	teristics								
V <sub>GS(th)</sub>	Gate Thr	eshold Voltage	VGS	<sub>S</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
R <sub>DS(on)</sub>		ain to Source On Resistance		$_{\rm S} = 10$ V, $I_{\rm D} = 12$ A		-	0.166	0.2	Ω
9FS	Forward	Transconductance		<sub>s</sub> = 20 V, I <sub>D</sub> = 12 A		-	30	-	S
Dynamic C	haracte	ristics							1
C <sub>iss</sub>	Input Capacitance				-	3240	4310	pF	
C <sub>oss</sub>		apacitance		$V_{\rm DS} = 25 \text{ V}, \text{ V}_{\rm GS} = 0 \text{ V},$		-	450	600	pF
C <sub>rss</sub>		Transfer Capacitance	f = '	f = 1 MHz	-	-	32	48	pF
Q <sub>g(tot)</sub>		e Charge at 10V	V	- 400 \/   - 24 A			65	85	nC
Q <sub>gs</sub>		Source Gate Charge		$V_{DS} = 400 \text{ V}, \text{ I}_{D} = 24 \text{ A},$ $V_{GS} = 10 \text{ V}$			18	_	nC
Q <sub>gd</sub>		Drain "Miller" Charge		, . <b>.</b> .	(Note 4,)	-	26	-	nC
Switching (	Charact	eristics							
-	1	Delay Time				-	49	108	ns
t <sub>d(on)</sub> t <sub>r</sub>		Rise Time	Vor	$V_{DD}$ = 250 V, I <sub>D</sub> = 24 A, $V_{GS}$ = 10 V, R <sub>G</sub> = 25 Ω (Note 4)		-	105	220	ns
		Delay Time					165	340	ns
t <sub>d(off)</sub> t <sub>f</sub>	Turn-Off	,				-	87	185	ns
					(1010-1)		0.		
s	Irce Diode Characteristics Maximum Continuous Drain to Source Diode Forward Current					-	-	24	Α
I <sub>SM</sub>		Pulsed Drain to Source Dio				-	-	96	Α
V <sub>SD</sub>		Source Diode Forward Voltag		<sub>s</sub> = 0 V, I <sub>SD</sub> = 24 A	1	-	-	1.4	V
t <sub>rr</sub>	Reverse I	Recovery Time		$V_{GS} = 0 V, I_{SD} = 24 A,$		-	264	-	ns
Q <sub>rr</sub>	Reverse I	Recovery Charge		$dI_{\rm F}/dt = 100  {\rm A}/{\mu s}$		-	1.4		μC

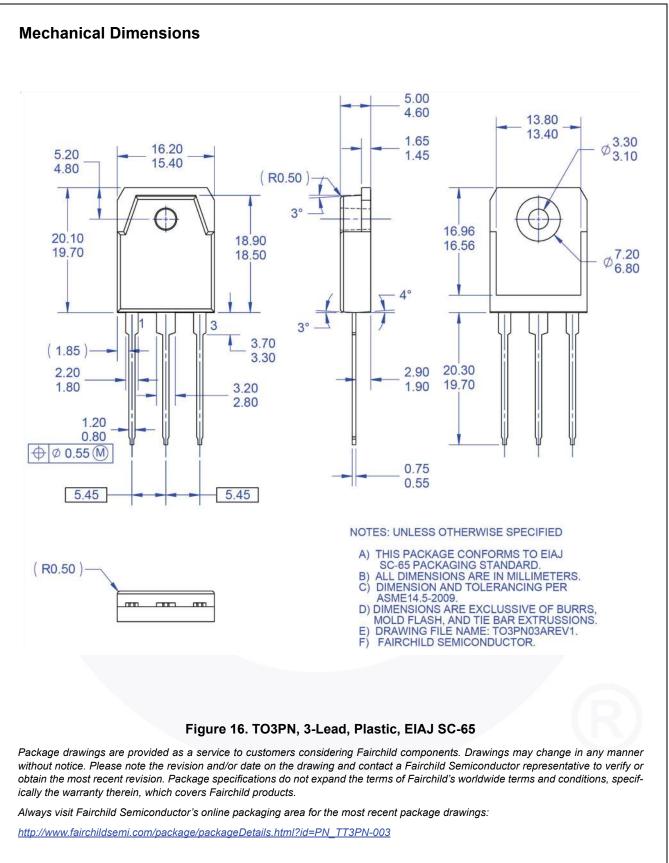














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